Silicon NPN Power Transistors 2SD1849

DESCRIPTION

- With TO-3PFa package
- High voltage,high speed
- Built-in damper diode
- Wide area of safe operation

APPLICATIONS

- Horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

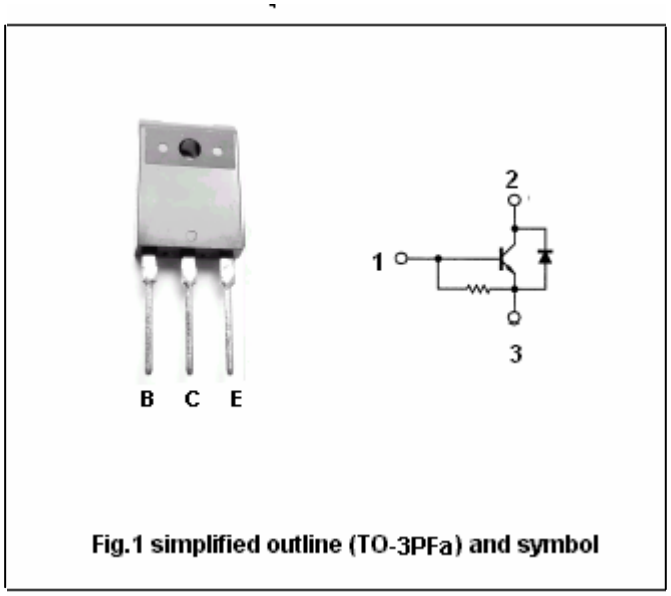

Fig.1 simplified outline (TO-3PFa) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		7	A
P_C	Collector power dissipation	T_a=25℃	3	W
		T_C=25℃	120	
T_j	Max.operating junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=500mA ;I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=6A; I_B=1.4A			8.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=6A; I_B=1.4A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=750V; I_E=0			10	μA
		V_{CB}=1500V; I_E=0			1.0	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	5		25	
h_{FE-2}	DC current gain	I_C=6A ; V_{CE}=10V	4			
f_T	Transition frequency	I_C=1A ; V_{CE}=10V;f=0.5MHz		2		MHz
V_F	Diode forward voltage	I_C=7A			2.0	V

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PACKAGE OUTLINE

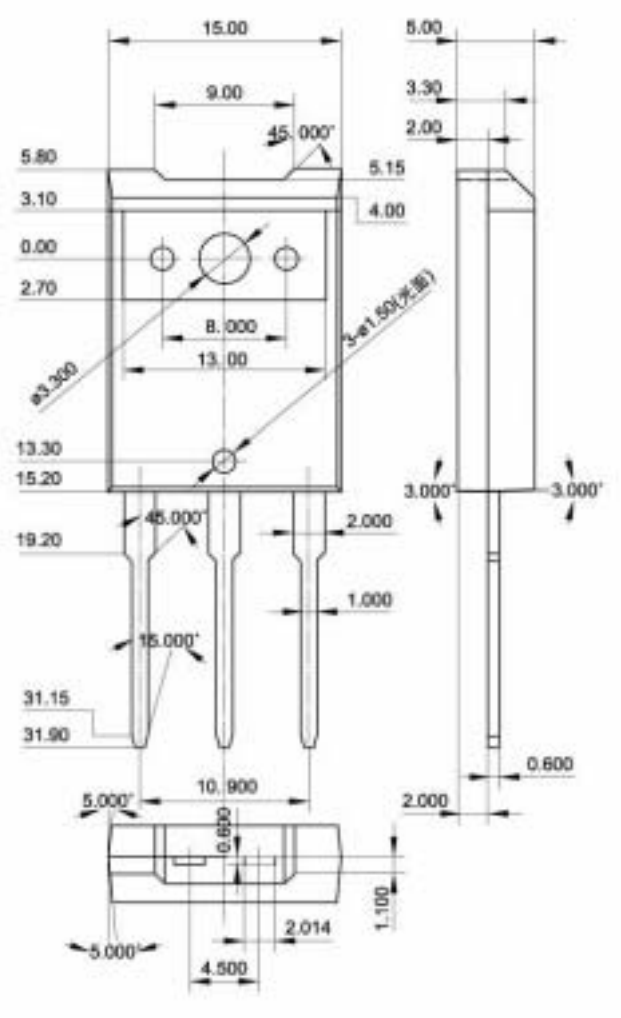

Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)